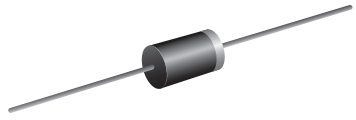
SB3150-SB3200

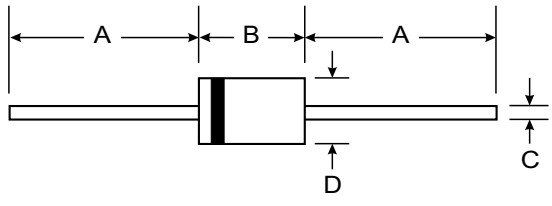
AXIAL LEADED SCHOTTKY BARRIER DIODE

VOLTAGE RANGE: 150-200V
CURRENT: 3.0 A

Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications





DO-201AD		
Dim	**Min**	**Max**
A	25.40	—
B	7.20	9.50
C	1.20	1.30
D	4.80	5.30
All Dimensions in mm		

Mechanical Data

- Case: DO-201AD, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 1.2 grams (approx.)
- Mounting Position: Any
- Marking: Type Number

RoHS COMPLIANT

Maximum Ratings and Electrical Characteristics

T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Number	*SYMBOLS*	SB3150	SB3200	UNITS
Maximum repetitive peak reverse voltage	V_{RRM}	150	200	VOLTS
Maximum RMS voltage	V_{RMS}	105	140	VOLTS
Maximum DC blocking voltage	V_{DC}	150	200	VOLTS
Maximum average forward rectified current 0.375”(9.5mm) lead length(see fig.1)	$I_{(AV)}$	3.0		Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	80.0		Amps
Maximum instantaneous forward voltage at 3.0A	V_F	0.95		Volts
Maximum DC reverse current T_A=25℃	I_R	0.2		mA
at rated DC blocking voltage T_A=100℃		2.0		
Typical junction capacitance (NOTE 1)	C_J	160		pF
Typical thermal resistance (NOTE 2)	$R_{\theta JA}$	40.0		°C/W
Operating junction temperature range	$T_{J,}$	-65 to +150		°C
Storage temperature range	T_{STG}	-65 to +150		°C

Note:1.Measured at 1MHz and applied reverse voltage of 4.0V D.C.

2.Thermal resistance from junction to ambient at 0.375”(9.5mm)lead length,P.C.B. mounted